

Brian Corbett

List of Publications by Year in descending order

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340
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126907

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168389

53
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340
all docs

340
docs citations

340
times ranked

3998
citing authors

#	ARTICLE	IF	CITATIONS
1	Wafer-scale integration of group III-V lasers on silicon using transfer printing of epitaxial layers. Nature Photonics, 2012, 6, 610-614.	31.4	218
2	737 Tb/s (96 x 3 x 256-Gb/s) mode-division-multiplexed DP-16QAM transmission with inline MM-EDFA. Optics Express, 2012, 20, B428.	3.4	156
3	Transfer print techniques for heterogeneous integration of photonic components. Progress in Quantum Electronics, 2017, 52, 1-17.	7.0	141
4	100 Gbit/s WDM transmission at 2 Åµm: transmission studies in both low-loss hollow core photonic bandgap fiber and solid core fiber. Optics Express, 2015, 23, 4946.	3.4	111
5	III-V-on-Si photonic integrated circuits realized using micro-transfer-printing. APL Photonics, 2019, 4, .	5.7	108
6	Micro-Light Emitting Diode: From Chips to Applications. Laser and Photonics Reviews, 2021, 15, 2000133.	8.7	108
7	Practical Design of Lensed Fibers for Semiconductor Laser Packaging Using Laser Welding Technique. Journal of Lightwave Technology, 2009, 27, 1533-1539.	4.6	99
8	Transfer-printing-based integration of a III-V-on-silicon distributed feedback laser. Optics Express, 2018, 26, 8821.	3.4	98
9	Heterogeneous III-V on silicon nitride amplifiers and lasers via microtransfer printing. Optica, 2020, 7, 386.	9.3	84
10	Analysis of Slot Characteristics in Slotted Single-Mode Semiconductor Lasers Using the 2-D Scattering Matrix Method. IEEE Photonics Technology Letters, 2006, 18, 2605-2607.	2.5	76
11	Single longitudinal mode ridge waveguide 1.3Åµm Fabry-Perot laser by modal perturbation. Electronics Letters, 1995, 31, 2181-2182.	1.0	74
12	Reconfigurable Modal Gain Control of a Few-Mode EDFA Supporting Six Spatial Modes. IEEE Photonics Technology Letters, 2014, 26, 1100-1103.	2.5	74
13	Discretely Tunable Semiconductor Lasers Suitable for Photonic Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 482-487.	2.9	56
14	Three mode Er ³⁺ ring-doped fiber amplifier for mode-division multiplexed transmission. Optics Express, 2013, 21, 10383.	3.4	56
15	Emerging optofluidic technologies for point-of-care genetic analysis systems: a review. Analytical and Bioanalytical Chemistry, 2009, 395, 621-636.	3.7	54
16	Carrier distribution in InGaN/GaN tricolor multiple quantum well light emitting diodes. Applied Physics Letters, 2009, 95, .	3.3	51
17	Hybrid Integration of the Wavelength-Tunable Laser With a Silicon Photonic Integrated Circuit. Journal of Lightwave Technology, 2013, 31, 3934-3942.	4.6	51
18	Micro-Transfer-Printed III-V-on-Silicon Band Semiconductor Optical Amplifiers. Laser and Photonics Reviews, 2020, 14, 1900364.	8.7	50

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19	20 Å— 960-Cb/s Space-division-multiplexed 32QAM transmission over 60 km few-mode fiber. Optics Express, 2014, 22, 749.	3.4	49
20	Characterization of Ge-on-Si virtual substrates and single junction GaAs solar cells. Semiconductor Science and Technology, 2006, 21, 775-780.	2.0	48
21	Measurement of linewidth enhancement factor in self-assembled quantum dot semiconductor lasers emitting at 1310nm. Electronics Letters, 2004, 40, 428.	1.0	47
22	InP-Based Active and Passive Components for Communication Systems at 2 ¼m. Journal of Lightwave Technology, 2015, 33, 971-975.	4.6	44
23	Silicon photonics fiber-to-the-home transceiver array based on transfer-printing-based integration of III-V photodetectors. Optics Express, 2017, 25, 14290.	3.4	44
24	A Novel Two-Section Tunable Discrete Mode Fabry-Pérot Laser Exhibiting Nanosecond Wavelength Switching. IEEE Journal of Quantum Electronics, 2008, 44, 331-337.	1.9	43
25	Dense WDM transmission at 2 ¼m enabled by an arrayed waveguide grating. Optics Letters, 2015, 40, 3308.	3.3	42
26	Plasmonic Schottky photodetector with metal stripe embedded into semiconductor and with a CMOS-compatible titanium nitride. Scientific Reports, 2019, 9, 6048.	3.3	41
27	GHz bandwidth semipolar (112) InGaN/GaN light-emitting diodes. Optics Letters, 2016, 41, 5752.	3.3	40
28	Low Noise Heterogeneous III-V-on-Silicon Nitride Mode-Locked Comb Laser. Laser and Photonics Reviews, 2021, 15, 2000485.	8.7	38
29	Time to Open the 2 ¼m Window?. Optics and Photonics News, 2019, 30, 42.	0.5	37
30	Transfer printing of fully formed thin film microscale GaAs lasers on silicon with a thermally conductive interface material. Laser and Photonics Reviews, 2015, 9, L17.	8.7	36
31	Transfer Printing of AlGaInAs/InP Etched Facet Lasers to Si Substrates. IEEE Photonics Journal, 2016, 8, 1-10.	2.0	36
32	Bloch surface wave structures for high sensitivity detection and compact waveguiding. Science and Technology of Advanced Materials, 2016, 17, 398-409.	6.1	36
33	Multi-level single mode 2D polymer waveguide optical interconnects using nano-imprint lithography. Optics Express, 2015, 23, 14630.	3.4	34
34	Polarization tunable transmission through plasmonic arrays of elliptical nanopores. Optics Express, 2012, 20, 25325.	3.4	33
35	Theoretical performance of multi-junction solar cells combining III-V and Si materials. Optics Express, 2012, 20, A754.	3.4	33
36	Micro-transfer-printed III-V-on-silicon C-band distributed feedback lasers. Optics Express, 2020, 28, 32793.	3.4	33

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37	High-Speed Substrate-Emitting Micro-Light-Emitting Diodes for Applications Requiring High Radiance. Applied Physics Express, 2013, 6, 022102.	2.4	32
38	Size-Dependent Bandwidth of Semipolar ($\text{In}_{1-x}\text{Ga}_x\text{N}$) Light-Emitting-Diodes. IEEE Photonics Technology Letters, 2018, 30, 439-442.	2.5	32
39	Simultaneous achievement of narrow pulse width and low pulse-to-pulse timing jitter in 13 μm passively mode-locked quantum-dot lasers. Optics Letters, 2006, 31, 3107.	3.3	31
40	Key enabling technologies for optical communications at 2000-nm. Applied Optics, 2018, 57, E64.	1.8	31
41	73.7 Tb/s (96 λ –3 λ –256-Gb/s) mode-division-multiplexed DP-16QAM transmission with inline MM-EDFA. , 2012, , .		31
42	40 Gb/s WDM Transmission Over 1.15-km HC-PBGF Using an InP-Based Mach-Zehnder Modulator at 2 μm . Journal of Lightwave Technology, 2016, 34, 1706-1711.	4.6	30
43	Phase dynamics of InAs \cdot GaAs quantum dot semiconductor optical amplifiers. Applied Physics Letters, 2007, 91, 263506.	3.3	29
44	200 μm -bit/s data transmission through 100 μm of plastic optical fibre with nitride LEDs. Electronics Letters, 2002, 38, 1457.	1.0	28
45	Thermoreflectance study of facet heating in semiconductor lasers. Materials Science in Semiconductor Processing, 2006, 9, 188-197.	4.0	28
46	Adhesive bonding for mechanically stacked solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 1080-1090.	8.1	28
47	Comparison of InGaAs and InAlAs sacrificial layers for release of InP-based devices. Optical Materials Express, 2017, 7, 4408.	3.0	28
48	Resonant cavity light emitting diode and detector using epitaxial liftoff. IEEE Photonics Technology Letters, 1993, 5, 1041-1043.	2.5	27
49	Vertical-cavity amplifying photonic switch at 1.5 μm . IEEE Photonics Technology Letters, 1996, 8, 1035-1037.	2.5	27
50	Characterization of germanium/silicon pn junction fabricated by low temperature direct wafer bonding and layer exfoliation. Applied Physics Letters, 2012, 100, .	3.3	27
51	Low-threshold lasing in novel microdisk geometries. IEEE Photonics Technology Letters, 1996, 8, 855-857.	2.5	26
52	A Multiwavelength Low-Power Wavelength-Locked Slotted Fabry-Perot Laser Source for WDM Applications. IEEE Photonics Technology Letters, 2007, 19, 744-746.	2.5	26
53	Surface recombination in dry etched AlGaAs/GaAs double heterostructure p-n mesa diodes. Applied Physics Letters, 1993, 62, 87-89.	3.3	25
54	Characterization of a tunable three-section slotted Fabry-Perot laser for advanced modulation format optical transmission. Optics Communications, 2011, 284, 1616-1621.	2.1	24

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55	Butterfly packaged high-speed and low leakage InGaAs quantum well photodiode for 2000nm wavelength systems. Electronics Letters, 2013, 49, 281-282.	1.0	24
56	High aspect ratio nano-fabrication of photonic crystal structures on glass wafers using chrome as hard mask. Nanotechnology, 2014, 25, 355301.	2.6	24
57	Monolithically integrated low linewidth comb source using gain switched slotted Fabry-Perot lasers. Optics Express, 2016, 24, 7960.	3.4	24
58	Integrated plasmonic circuitry on a vertical-cavity surface-emitting semiconductor laser platform. Nature Communications, 2016, 7, 12409.	12.8	24
59	CMOS-Compatible Titanium Nitride for On-Chip Plasmonic Schottky Photodetectors. ACS Omega, 2019, 4, 17223-17229.	3.5	24
60	Direct visualization of phase-matched efficient second harmonic and broadband sum frequency generation in hybrid plasmonic nanostructures. Light: Science and Applications, 2020, 9, 180.	16.6	24
61	InAlAs solar cell on a GaAs substrate employing a graded In _x Ga _{1-x} As InP metamorphic buffer layer. Applied Physics Letters, 2013, 102, .	3.3	23
62	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	9.1	23
63	Transfer Printing for Silicon Photonics. Semiconductors and Semimetals, 2018, 99, 43-70.	0.7	23
64	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride waveguides for near-infrared applications. Optics Express, 2020, 28, 21275.	3.4	23
65	Experimental observation of traveling waves in the transverse section of a laser. Optics Letters, 2001, 26, 1556.	3.3	22
66	Free-carrier effect on index change in 1.3 μ m quantum-dot lasers. Electronics Letters, 2005, 41, 416.	1.0	22
67	Fast Wavelength Switching Lasers Using Two-Section Slotted Fabry-Perot Structures. IEEE Photonics Technology Letters, 2006, 18, 2105-2107.	2.5	21
68	Enhanced performance of graphene-based electro-absorption waveguide modulators by engineered optical modes. Journal Physics D: Applied Physics, 2015, 48, 235101.	2.8	21
69	Novel droplet near-field transducer for heat-assisted magnetic recording. Nanophotonics, 2015, 4, 503-510.	6.0	20
70	A configuration design based method for platform commonization for product families. Artificial Intelligence for Engineering Design, Analysis and Manufacturing: AIEDAM, 2004, 18, 21-39.	1.1	19
71	On the specific contact resistance of metal contacts to p-type GaN. Semiconductor Science and Technology, 2006, 21, 1738-1742.	2.0	19
72	Ge/Si heterojunction photodiodes fabricated by low temperature wafer bonding. Optics Express, 2013, 21, 17309.	3.4	19

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73	Fabrication of GaN-Based Resonant Cavity LEDs. <i>Physica Status Solidi A</i> , 2002, 192, 348-353.	1.7	18
74	Fabry-Pérot Laser Characterization Based on the Amplified Spontaneous Emission Spectrum and the Fourier Series Expansion Method. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 1356-1363.	2.9	18
75	Design, Characterization, and Applications of Index-Patterned Fabry-Pérot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 1621-1631.	2.9	18
76	High Bandwidth Freestanding Semipolar (11 $\bar{2}$) InGaN/GaN Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , 2016, 8, 1-8.	2.0	18
77	Narrow bandwidth long wavelength resonant cavity photodiodes. <i>Electronics Letters</i> , 1993, 29, 2148.	1.0	17
78	Experimental Characterisation of GaN-Based Resonant Cavity Light Emitting Diodes. <i>Physica Status Solidi A</i> , 2002, 192, 97-102.	1.7	17
79	Modeling the Effects of Interface Traps on the Static and Dynamic Characteristics of Ge/Si Avalanche Photodiodes. <i>IEEE Journal of Quantum Electronics</i> , 2011, 47, 849-857.	1.9	17
80	Strategies for integration of lasers on silicon. <i>Semiconductor Science and Technology</i> , 2013, 28, 094001.	2.0	17
81	Semipolar (112) InGaN light-emitting diodes grown on chemically-mechanically polished GaN templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 2196-2200.	1.8	17
82	Thermal Analysis of InP Lasers Transfer Printed to Silicon Photonics Substrates. <i>Journal of Lightwave Technology</i> , 2018, 36, 5935-5941.	4.6	17
83	High power surface emitting InGaN superluminescent light-emitting diodes. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	17
84	Microthermography of diode lasers: The impact of light propagation on image formation. <i>Journal of Applied Physics</i> , 2009, 105, 014502.	2.5	16
85	Wavelength Tunable Laser Using an Interleaved Rear Reflector. <i>IEEE Photonics Technology Letters</i> , 2010, 22, 54-56.	2.5	16
86	Low defect large area semi-polar (112) GaN grown on patterned (113) silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1104-1108.	1.5	16
87	Ultrasonically Powered Compact Implantable Dust for Optogenetics. <i>IEEE Transactions on Biomedical Circuits and Systems</i> , 2020, 14, 583-594.	4.0	16
88	Multiwavelength array of single-frequency stabilized Fabry-Perot lasers. <i>IEEE Journal of Quantum Electronics</i> , 2005, 41, 490-494.	1.9	15
89	Laser and detector using integrated reflector for photonic integration. <i>Electronics Letters</i> , 2008, 44, 1017.	1.0	15
90	Zero-Bias High-Speed Edge-Coupled Unitraveling-Carrier InGaAs Photodiode. <i>IEEE Photonics Technology Letters</i> , 2010, 22, 1747-1749.	2.5	15

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91	InGaAs Surface Normal Photodiode for 2 μm Optical Communication Systems. IEEE Photonics Technology Letters, 2015, 27, 1469-1472.	2.5	15
92	80°C continuous wave operation of AlGaInP based visible VCSEL. Electronics Letters, 2002, 38, 222.	1.0	14
93	Integration of AllnGaAs-MQW Fabry-Perot Lasers With Emission at Two Wavelength Ranges via Quantum-Well Intermixing. IEEE Photonics Technology Letters, 2011, 23, 27-29.	2.5	14
94	Investigation of active filter using injection-locked slotted Fabry-Perot semiconductor laser. Applied Optics, 2012, 51, 7357.	1.8	14
95	Reflectivity Measurements of Intracavity Defects in Laser Diodes. IEEE Journal of Quantum Electronics, 2004, 40, 10-17.	1.9	13
96	Determination of Internal Loss and Quasi-Fermi Level Separation From the Amplified Spontaneous Emission Spectrum of Fabry-Perot Semiconductor Lasers. IEEE Photonics Technology Letters, 2006, 18, 1910-1912.	2.5	13
97	Broadband quantum dot micro-light-emitting diodes with parabolic sidewalls. Applied Physics Letters, 2008, 92, 123501.	3.3	13
98	10 Gb/s InP-based Mach-Zehnder modulator for operation at 2 μm wavelengths. Optics Express, 2015, 23, 10905.	3.4	13
99	Study of TiN nanodisks with regard to application for Heat-Assisted Magnetic Recording. MRS Advances, 2016, 1, 317-326.	0.9	13
100	InAlN-based LEDs emitting in the near-UV region. Japanese Journal of Applied Physics, 2019, 58, SCCB33.	1.5	13
101	Inductively coupled plasma deep etching of InP/InGaAsP in Cl ₂ /CH ₄ /H ₂ based chemistries with the electrode at 20°C. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 051208.	1.2	12
102	Design and fabrication tolerance analysis of multimode interference couplers. Optics Communications, 2015, 340, 26-32.	2.1	12
103	<title>Development of a red VCSEL-to-plastic fiber module for use in parallel optical data links</title>. , 2000, , .		11
104	Performance characteristics of quasi-single longitudinal-mode Fabry-Perot lasers. IEEE Photonics Technology Letters, 1996, 8, 1127-1129.	2.5	10
105	Tuneable VCSEL aiming for the application in interconnects and short haul systems. , 2011, , .		10
106	Growth optimization and characterization of lattice-matched Al _{0.82} In _{0.18} N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10
107	81 Gb/s WDM transmission at 2 μm over 1.15 km of low-loss hollow core photonic bandgap fiber. , 2014, , .		10
108	Semipolar (2021...3) nitrides grown on 3C-SiC/(001) Si substrates. Semiconductor Science and Technology, 2015, 30, 125007.	2.0	10

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109	4×25 Gbps Polarization Diversity Silicon Photonics Receiver With Transfer Printed III-V Photodiodes. IEEE Photonics Technology Letters, 2019, 31, 287-290.	2.5	10
110	Spectral characteristics of single-In/sub 0.7/Ga/sub 0.3/As quantum-well microring lasers. IEEE Photonics Technology Letters, 1998, 10, 3-5.	2.5	9
111	Focusing properties of high brightness gain tailored broad-area semiconductor lasers. IEEE Photonics Technology Letters, 2002, 14, 9-11.	2.5	9
112	High injection and carrier pile-up in lattice matched InGaAs/InP PN diodes for thermophotovoltaic applications. Journal of Applied Physics, 2004, 95, 2809-2815.	2.5	9
113	Measurement of linewidth enhancement factors for InGaAlAs laser diode by Fourier series expansion method. Electronics Letters, 2007, 43, 1145.	1.0	9
114	On-chip optical phase locking of single growth monolithically integrated slotted fabry perot lasers. Optics Express, 2013, 21, 17315.	3.4	9
115	First demonstration of a $2\frac{1}{4}$ m few-mode TDFA for mode division multiplexing. Optics Express, 2014, 22, 10544.	3.4	9
116	Nanoimprint Lithography-Based Fabrication of Plasmonic Array of Elliptical Nanoholes for Dual-Wavelength, Dual-Polarisation Refractive Index Sensing. Plasmonics, 2019, 14, 951-959.	3.4	9
117	S-MRUT: Sected-Multiring Ultrasonic Transducer for Selective Powering of Brain Implants. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 191-200.	3.0	9
118	Methane sensing with a novel micromachined single-frequency Fabry-Perot laser diode emitting at 1331 nm. IEEE Photonics Technology Letters, 1997, 9, 357-359.	2.5	8
119	Origin of power fluctuations in GaN resonant-cavity light-emitting diodes. Optics Express, 2004, 12, 736.	3.4	8
120	Loss analysis and increasing of the fabrication tolerance of resonant coupling by tapering the mode beating section. Optical and Quantum Electronics, 2011, 42, 521-529.	3.3	8
121	Compact Electroabsorption Modulators for Photonic Integrated Circuits, Using an Isolated Pedestal Contact Scheme. IEEE Photonics Technology Letters, 2012, 24, 356-358.	2.5	8
122	Monolithic Integration of Single Facet Slotted Laser, SOA, and MMI Coupler. IEEE Photonics Technology Letters, 2013, 25, 257-260.	2.5	8
123	Polarization matching design of InGaN-based semi-polar quantum wells-A case study of $(112\hat{A}^2)$ orientation. Applied Physics Letters, 2014, 104, .	3.3	8
124	AlInGaAs surface normal photodiode for 2 \hat{A} um optical communication systems. , 2015, , .		8
125	Role of substrate quality on the performance of semipolar $(112\hat{A}^2)$ InGaN light-emitting diodes. Journal of Applied Physics, 2016, 120, .	2.5	8
126	Development of semipolar $(11\text{-}22)$ LEDs on GaN templates. Proceedings of SPIE, 2016, , .	0.8	8

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127	Study of high order plasmonic modes on ceramic nanodisks. Optics Express, 2017, 25, 5244.	3.4	8
128	Edge-Coupling of O-Band InP Etched-Facet Lasers to Polymer Waveguides on SOI by Micro-Transfer-Printing. IEEE Journal of Quantum Electronics, 2020, 56, 1-8.	1.9	8
129	Characterization of bulk and surface currents in strain-balanced InGaAs quantum-well mesa diodes. Applied Physics Letters, 2004, 85, 6033-6035.	3.3	7
130	Length dependence of feedback sensitivity of InAs ⁺ GaAs quantum dot lasers. Electronics Letters, 2005, 41, 911.	1.0	7
131	Transition From Perturbed to Coupled-Cavity Behavior With Asymmetric Spectral Emission in Ridge Lasers Emitting at 1.55 μm . IEEE Photonics Technology Letters, 2007, 19, 58-60.	2.5	7
132	Modal Analysis of Large Spot Size, Low Output Beam Divergence Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2007, 19, 916-918.	2.5	7
133	Free-standing gallium nitride Schottky diode characteristics and stability in a high-temperature environment. Semiconductor Science and Technology, 2009, 24, 125008.	2.0	7
134	Comparative study of (0001) and $(11\bar{1}2)$ InGaN based light emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ10.	1.5	7
135	Exciton localization in polar and semipolar $(11\bar{2}\dots 2)$ In _{0.2} Ga _{0.8} N/GaN multiple quantum wells. Semiconductor Science and Technology, 2016, 31, 085006.	2.0	7
136	Surface emitting 1.5 μm multi-quantum well LED on epitaxial lateral overgrowth InP/Si. Optical Materials Express, 2020, 10, 1714.	3.0	7
137	<title>Gas sensing using IR laser diode sources</title>. , 1997, , .		6
138	Low-stress hybridisation of emitters, detectors and driver circuitry on a silicon motherboard for optoelectronic interconnect architecture. Materials Science in Semiconductor Processing, 2000, 3, 449-453.	4.0	6
139	Lasing from semiconductor microring on the end of an optical fiber. Applied Physics Letters, 2002, 81, 808-810.	3.3	6
140	LED flip-chip assembly with electroplated AuSn alloy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2907-2911.	0.8	6
141	Low-resistance Ni-based Schottky diodes on freestanding n-GaN. Applied Physics Letters, 2007, 91, 162103.	3.3	6
142	Fabrication and characterization of three-dimensional silver/air inverted opal photonic crystals. Journal of Materials Chemistry, 2010, 20, 7870.	6.7	6
143	Individually addressable optoelectronic arrays for optogenetic neural stimulation. , 2011, , .		6
144	Current transport through AlInN/GaN multilayers used as n-type cladding layers in edge emitting laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2378-2380.	0.8	6

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145	Cleaved-facet violet laser diodes with lattice-matched Al _{0.82} In _{0.18} N/GaN multilayers as n-cladding. Applied Physics Letters, 2011, 98, 201112.	3.3	6
146	Surface Plasmon assisted extraordinary transmission in metallic nanohole arrays and its suitability as a bio-sensor. Journal of Physics: Conference Series, 2011, 307, 012005.	0.4	6
147	Dual resonance approach to decoupling surface and bulk attributes in photonic crystal biosensor. Optics Letters, 2014, 39, 6213.	3.3	6
148	Three-coherent-output narrow-linewidth and tunable single frequency 1x2 multi-mode-interferometer laser diode. Optics Express, 2016, 24, 5846.	3.4	6
149	Microtransfer Printing High-Efficiency GaAs Photovoltaic Cells onto Silicon for Wireless Power Applications. Advanced Materials Technologies, 2020, 5, 2000048.	5.8	6
150	III-V/Si PICs based on micro-transfer-printing. , 2019, , .		6
151	Transfer Printing of Roughened GaN-Based Light-Emitting Diodes into Reflective Trenches for Visible Light Communication. Advanced Photonics Research, 2022, 3, .	3.6	6
152	Dark currents in pin photodetectors fabricated by preprocessing and postprocessing techniques of epitaxial liftoff. Electronics Letters, 1995, 31, 1382-1383.	1.0	5
153	Quantum well intermixing in AlInGaAs MQW structures through impurity-free vacancy method. , 2010, , .		5
154	Fast wavelength switching in interleaved rear reflector laser. , 2010, , .		5
155	High index contrast optical platform using gallium phosphide on sapphire: an alternative to SOI?. Proceedings of SPIE, 2012, , .	0.8	5
156	SiNx-induced intermixing in AlInGaAs/InP quantum well through interdiffusion of group III atoms. Journal of Applied Physics, 2012, 112, .	2.5	5
157	Multiple coherent outputs from single growth monolithically integrated injection locked tunable lasers. , 2012, , .		5
158	WDM Transmission at 2 ¹ / ₄ μm over Low-Loss Hollow Core Photonic Bandgap Fiber. , 2013, , .		5
159	Stable locking phase limits of optically injected semiconductor lasers. Optics Express, 2013, 21, 30126.	3.4	5
160	Over 20MHz modulation bandwidth on 250nm emission of AlGaIn micro-LEDs. Electronics Letters, 2015, 51, 354-355.	1.0	5
161	Low-power-consumption optical interconnect on silicon by transfer-printing for used in opto-isolators. Journal Physics D: Applied Physics, 2019, 52, 064001.	2.8	5
162	Gain-switched dual frequency comb at 2 μm. Optics Express, 2022, 30, 5213.	3.4	5

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163	Low-divergence laser structures for cost-effective fiber coupling applications. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 571-576.	2.9	4
164	A novel single frequency stabilized Fabry-Perot laser diode at 1590 nm for gas sensing. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2002, 58, 2433-2438.	3.9	4
165	Red and green resonant cavity LEDs for datacom applications. , 2003, 4876, 176.		4
166	A Novel Two-Section Tunable Slotted Fabry-Perot Laser Exhibiting ns Wavelength Switching. , 2007, , .		4
167	Fast Switching Tunable Laser Sources for Wavelength Division Multiplexing in Passive Optical Access Networks. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	4
168	AlInN optical confinement layers for edge emitting group III-nitride laser structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S897.	0.8	4
169	Heterodyne Method for Time Resolved Spectral Analysis of Fast Laser Wavelength Switching. IEEE Photonics Technology Letters, 2009, 21, 1517-1519.	2.5	4
170	Characterization of a Novel Three-Section Tunable Slotted Fabry-Perot Laser. , 2010, , .		4
171	Thermal stability of SiC Schottky diode anode and cathode metalisations after 1000h at 350°C. Microelectronics Reliability, 2011, 51, 904-908.	1.7	4
172	Ge/Si p-n Diode Fabricated by Direct Wafer Bonding and Layer Exfoliation. ECS Transactions, 2012, 45, 131-139.	0.5	4
173	Sub 10 ps Carrier Response Times in Electroabsorption Modulators Using Quantum Well Offsetting. IEEE Journal of Quantum Electronics, 2012, 48, 1467-1475.	1.9	4
174	TE/TM-mode pass polarizers and splitter based on an asymmetric twin waveguide and resonant coupling. Optical and Quantum Electronics, 2012, 44, 175-181.	3.3	4
175	Polymer-based optical interconnects using nanoimprint lithography. , 2013, , .		4
176	Multimode EDFA performance in mode-division multiplexed transmission systems. , 2013, , .		4
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